

500 mA, 50 V NPN resistor-equipped transistors

Rev. 1 — 15 May 2014

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package			PNP Package	
	Nexperia	JEITA	JEDEC	complement	configuration
PDTD143ET	SOT23	-	TO-236AB	PDTB143ET	small
PDTD143XT				PDTB143XT	
PDTD114ET				PDTB114ET	

1.2 Features

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- ± 10 % resistor ratio tolerance
- AEC-Q101 qualified
- High temperature applications up to 175 °C

1.3 Applications

- IC inputs control
- Cost-saving alternative to BC807 or BC817 series transistors in digital applications

Switching loads



1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	500	mA
R1	bias resistor 1 (input)	'	'	1	'	
	PDTD143ET			4.7		kΩ
	PDTD143XT			4.7		kΩ
	PDTD114ET			10		kΩ
R2	bias resistor 2 (base-emitter)	'	'	1	'	
	PDTD143ET			4.7		kΩ
	PDTD143XT			10		kΩ
	PDTD114ET			10		kΩ

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	input (base)		
2	GND (emitter)		3
3	output (collector)	1	1 R1 R2
			sym007

3. Ordering information

Table 4. Ordering information

Type number	Package	ackage						
	Name	Description	Version					
PDTD1xxxT series	TO-236AB	plastic surface-mounted package; 3 leads	SOT23					

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTD143ET	*4Z
PDTD143XT	*5Z
PDTD114ET	*10

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

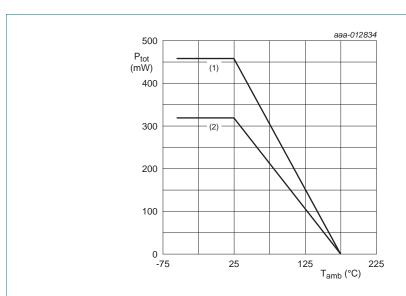
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector				
	PDTD143ET			-	10	V
	PDTD143XT			-	7	V
	PDTD114ET			-	10	V
VI	input voltage					
	PDTD143ET			-10	+30	V
	PDTD143XT			-7	+30	V
	PDTD114ET			-10	+50	V
Io	output current			-	500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	320	mW
			[2]	-	460	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	+175	°C
T _{stg}	storage temperature			-55	+175	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



- (1) FR4 PCB, 4-layer copper, standard footprint
- (2) FR4 PCB, single-sided copper, standard footprint.

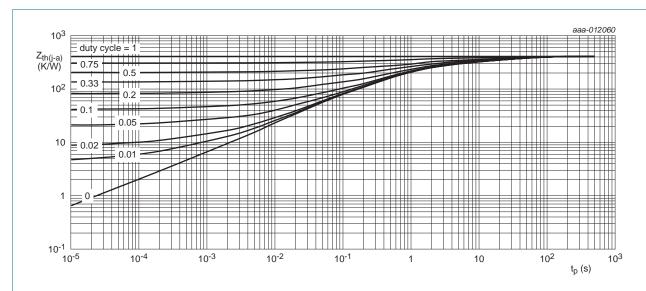
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

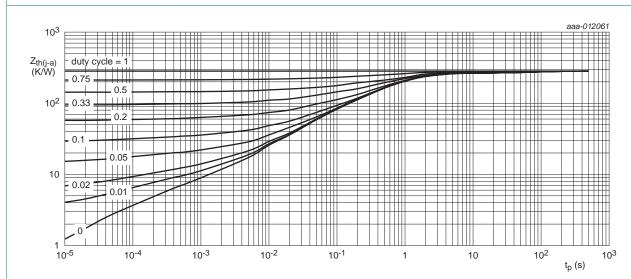
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}		in free air [1]	-	-	470	K/W
	to ambient	[2]	-	-	327	K/W

- 1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23/TO-236AB; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23/TO-236AB; typical values

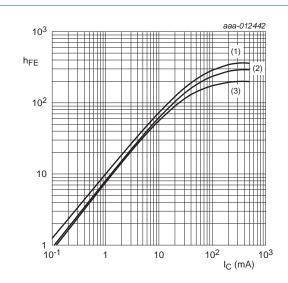
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 40 V; I _E = 0 A	-	-	100	nA
	current	V _{CB} = 50 V; I _E = 0 A	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; I_B = 0 \text{ A}$	-	-	0.5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A				
	PDTD143ET		-	-	0.9	mA
	PDTD143XT		-	-	0.6	mA
	PDTD114ET		-	-	0.4	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$		1	1	
	PDTD143ET		60	-	-	
	PDTD143XT		70	-	-	
	PDTD114ET		70	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$		1	1	
, ,	PDTD143ET		0.6	0.9	1.5	V
	PDTD143XT		0.5	0.75	1.1	V
	PDTD114ET		0.6	1.0	1.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$				'
	PDTD143ET		1.0	1.6	2.2	V
	PDTD143XT		1.0	1.25	2.0	V
	PDTD114ET		1.0	1.9	3.0	V
R1	bias resistor 1 (input)			•		'
	PDTD143ET		3.3	4.7	6.1	kΩ
	PDTD143XT		3.3	4.7	6.1	kΩ
	PDTD114ET		7.0	10	13	kΩ
R2/R1	bias resistor ratio			•		'
	PDTD143ET		0.9	1	1.1	
	PDTD143XT		1.91	2.13	2.34	
	PDTD114ET		0.9	1.0	1.1	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	7	-	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 50 \text{ mA;}$ f = 100 MHz	-	225	-	MHz

^[1] Characteristics of built-in transistor.



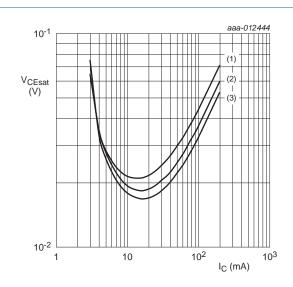
$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. PDTD143ET: DC current gain as a function of collector current; typical values



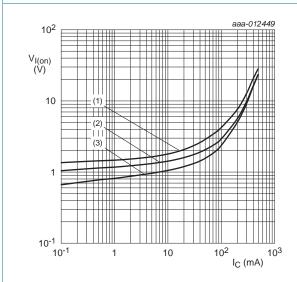
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. PDTD143ET: Collector-emitter saturation voltage as a function of collector current; typical values



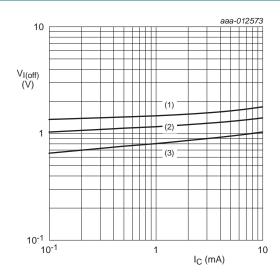


(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. PDTD143ET: On-state input voltage as a function of collector current; typical values



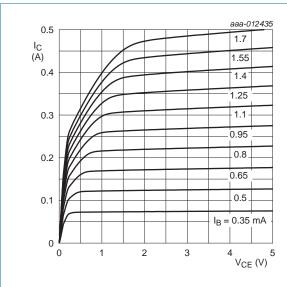
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

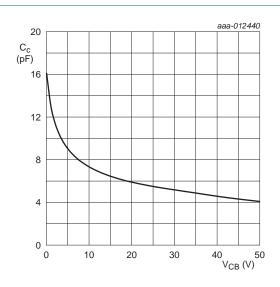
(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. PDTD143ET: Off-state input voltage as a function of collector current; typical values



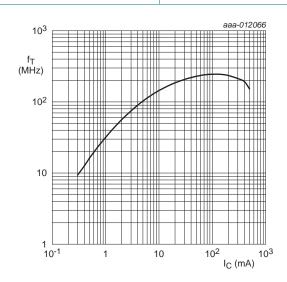
 $T_{amb} = 25 \, ^{\circ}C$

Fig 8. PDTD143ET: Collector current as a function of collector-emitter voltage; typical values



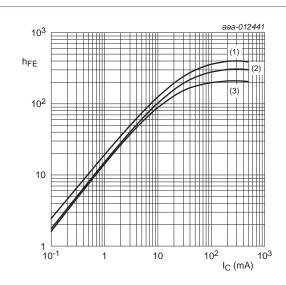
 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 9. PDTD143ET: Collector capacitance as a function of collector-base voltage; typical values



 V_{CE} = 5 V; T_{amb} = 25 °C

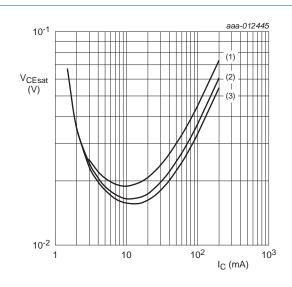
Fig 10. PDTD143ET: Transition frequency as a function of collector current; typical values of built-in transistor



$$V_{CE} = 5 V$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

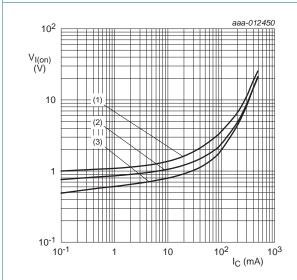
Fig 11. PDTD143XT: DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

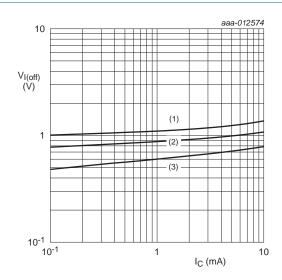
Fig 12. PDTD143XT: Collector-emitter saturation voltage as a function of collector current; typical values





- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 13. PDTD143XT: On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 14. PDTD143XT: Off-state input voltage as a function of collector current; typical values

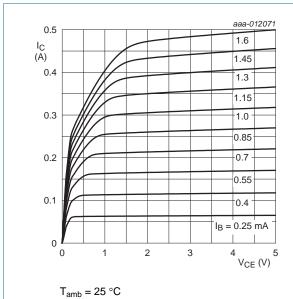


Fig 15. PDTD143XT: Collector current as a function of collector-emitter voltage; typical values

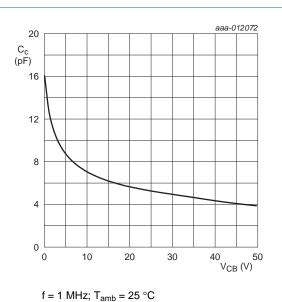
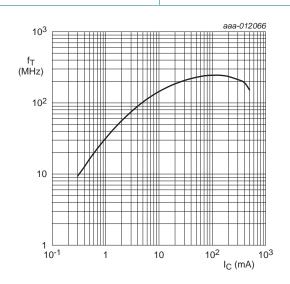


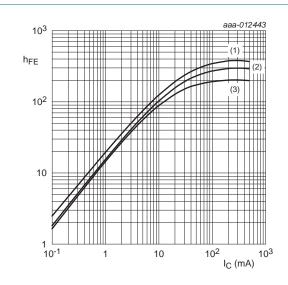
Fig 16. PDTD143XT: Collector capacitance as a function of collector-base voltage; typical

values



 V_{CE} = 5 V; T_{amb} = 25 °C

Fig 17. PDTD143XT: Transition frequency as a function of collector current; typical values of built-in transistor



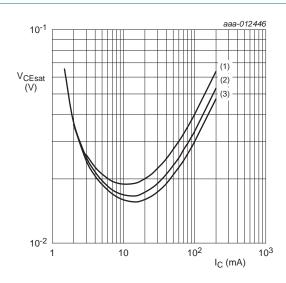
$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 18. PDTD114ET: DC current gain as a function of collector current; typical values



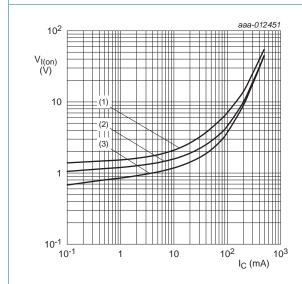
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 19. PDTD114ET: Collector-emitter saturation voltage as a function of collector current; typical values



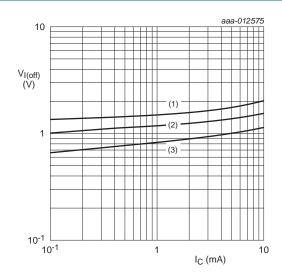


(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 20. PDTD114ET: On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 21. PDTD114ET: Off-state input voltage as a function of collector current; typical values

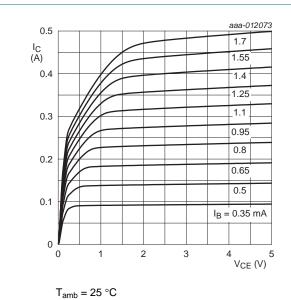
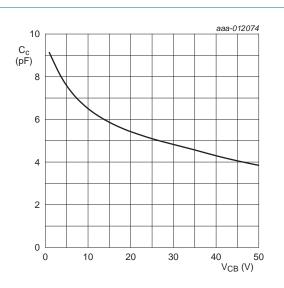
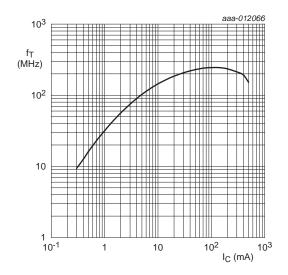


Fig 22. PDTD114ET: Collector current as a function of collector-emitter voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 23. PDTD114ET: Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE} = 5 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}$

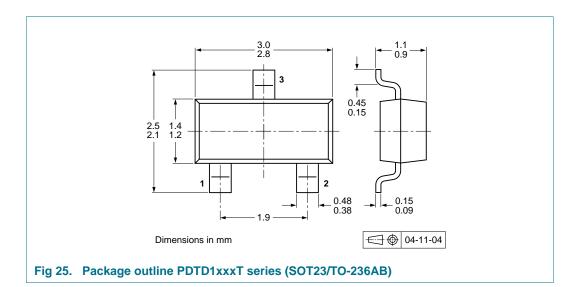
Fig 24. PDTD114ET: Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

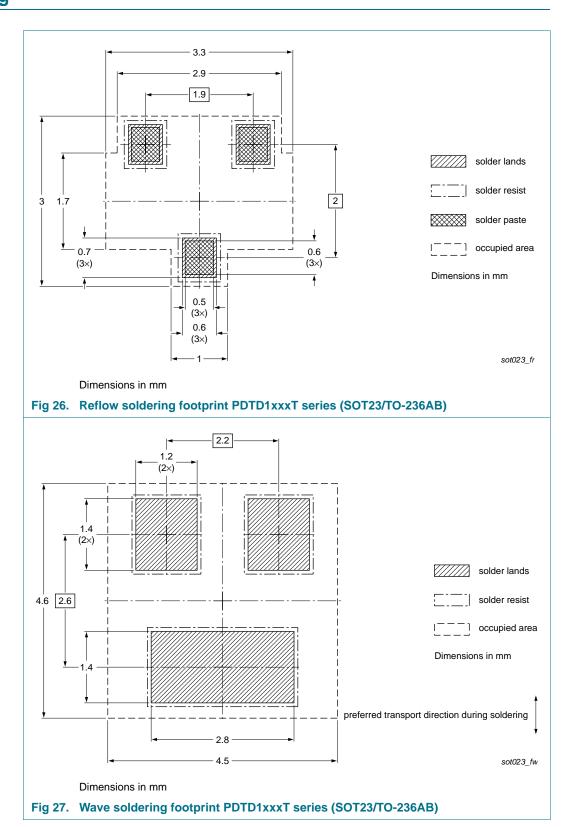
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Soldering



500 mA, 50 V NPN resistor-equipped transistors

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTD1XXXT_SER v.1	20140515	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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500 mA, 50 V NPN resistor-equipped transistors

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For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

500 mA, 50 V NPN resistor-equipped transistors

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NSBC113EF3T5G NSBC124XF3T5G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN1306(TE85L,F)

BCR129SH6327XTSA1 TTEPROTOTYPE79 DTA113EET1G EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBA124XF3T5G

NSBC123EF3T5G NSBC143ZPDP6T5G NSBC144TF3T5G NSVMUN5113DW1T3G SMUN2214T1G FMA7AT148 MUN2135T1G

DTC114EUA-TP 2SA1344-TB-E 4MN10MH-TL-E 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G

SMUN5113T1G SMUN2111T1G DTC124ECA-TP DTA114ECA-TP DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G

NSVDTC143ZM3T5G SMUN5335DW1T2G